

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) ~~A substrate assembly for a display~~ A semiconductor device comprising:

a substrate; and

~~a film~~ a first insulating film provided over said substrate and comprising aluminum nitride and oxygen;

a second insulating film comprising silicon oxide formed on the first insulating film; and

a thin film transistor formed over said second insulating film,

wherein:

said thin film transistor comprises a crystalline semiconductor film including a channel region;

said first insulating film has a thermal conductivity of  $200 \text{ Wm}^{-1}\text{K}^{-1}$  or more; and

said first insulating film has a thickness of  $500 \text{ \AA}$  to  $3 \text{ }\mu\text{m}$ .

2. (Currently Amended) ~~A substrate assembly for a display~~ A semiconductor device comprising:

a substrate; and

an AINO film provided over said substrate;

an insulating film comprising silicon oxide formed on the AINO film; and

a thin film transistor formed over said insulating film,

wherein:

said thin film transistor comprises a crystalline semiconductor film including a channel region;

said AlNO film has a thermal conductivity of  $200 \text{ Wm}^{-1}\text{K}^{-1}$  or more; and  
said AlNO film has a thickness of  $500 \text{ \AA}$  to  $3 \text{ }\mu\text{m}$ .

3. (Currently Amended) ~~A substrate assembly for a display~~ A semiconductor device comprising:

a substrate; and

an AlN film containing oxygen provided over said substrate;

an insulating film comprising silicon oxide formed on the AlN film; and

a thin film transistor formed over said insulating film,

wherein:

said thin film transistor comprises a crystalline semiconductor film including a channel region;

said AlN film has a thermal conductivity of  $200 \text{ Wm}^{-1}\text{K}^{-1}$  or more; and

said AlN film has a thickness of  $500 \text{ \AA}$  to  $3 \text{ }\mu\text{m}$ .

4. (Currently Amended) ~~A substrate assembly for a display~~ A semiconductor device comprising:

a substrate; and

~~a film~~ a first insulating film provided over said substrate and comprising aluminum nitride and oxygen;

a second insulating film comprising silicon oxide formed on the first insulating film; and

a thin film transistor formed over said second insulating film,

wherein:

said oxygen is contained in said insulating film at 0.001 to 10 atomic percent;

said thin film transistor comprises a crystalline semiconductor film including a channel region;

said first insulating film has a thermal conductivity of  $200 \text{ Wm}^{-1}\text{K}^{-1}$  or more; and

said first insulating film has a thickness of 500 Å to 3 μm.

5. (Currently Amended) ~~A substrate assembly~~ A semiconductor device  
according to claim 1 wherein said substrate comprises glass.

6. (Currently Amended) ~~A substrate assembly~~ A semiconductor device  
according to claim 2 wherein said substrate comprises glass.

7. (Currently Amended) ~~A substrate assembly~~ A semiconductor device  
according to claim 3 wherein said substrate comprises glass.

8. (Currently Amended) ~~A substrate assembly~~ A semiconductor device  
according to claim 4 wherein said substrate comprises glass.

9.-17. (Canceled)

18. (Original) A substrate assembly according to claim 2 wherein said AlNO  
film is an insulating film.

19. (Original) A substrate assembly according to claim 3 wherein said AlN film  
is an insulating film.

20. (Original) A substrate assembly according to claim 4 wherein said film  
comprising the aluminum nitride and the oxygen is an insulating film.

21. (New) A semiconductor device comprising:  
a substrate;

a first insulating film provided over said substrate and comprising aluminum nitride and oxygen;

a second insulating film comprising silicon oxide formed on the first insulating film;

a semiconductor film comprising crystalline silicon formed over the second insulating film, said semiconductor film having a channel region;

a gate insulating film formed over the semiconductor film; and

a gate electrode formed over the channel region with the gate insulating film interposed therebetween,

wherein:

said first insulating film has a thermal conductivity of  $200 \text{ Wm}^{-1}\text{K}^{-1}$  or more; and

said first insulating film has a thickness of  $500 \text{ \AA}$  to  $3 \text{ }\mu\text{m}$ .

22. (New) A semiconductor device comprising:

a substrate;

a first insulating film provided over said substrate and comprising aluminum nitride and oxygen; and

a second insulating film comprising silicon oxide formed on the first insulating film;

a semiconductor film comprising crystalline silicon formed over the second insulating film, said semiconductor film having a channel region;

a gate insulating film formed over the semiconductor film; and

a gate electrode formed over the channel region with the gate insulating film interposed therebetween,

wherein:

said oxygen is contained in said film at 0.001 to 10 atomic percent;

said first insulating film has a thermal conductivity of  $200 \text{ Wm}^{-1}\text{K}^{-1}$  or more; and

said first insulating film has a thickness of  $500 \text{ \AA}$  to  $3 \text{ }\mu\text{m}$ .

23. (New) A semiconductor device according to claim 21, wherein said substrate comprises glass.

24. (New) A semiconductor device according to claim 22, wherein said substrate comprises glass.

25. (New) A semiconductor device according to claim 21, wherein said gate insulating film comprises a first film comprising silicon oxide and a second film comprising aluminum nitride.

26. (New) A semiconductor device according to claim 22, wherein said gate insulating film comprises a first film comprising silicon oxide and a second film comprising aluminum nitride.

27. (New) A semiconductor device according to claim 1, wherein said semiconductor device is a display device.

28. (New) A semiconductor device according to claim 2, wherein said semiconductor device is a display device.

29. (New) A semiconductor device according to claim 3, wherein said semiconductor device is a display device.

30. (New) A semiconductor device according to claim 4, wherein said semiconductor device is a display device.

31. (New) A semiconductor device according to claim 21, wherein said semiconductor device is a display device.

32. (New) A semiconductor device according to claim 22, wherein said semiconductor device is a display device.

33. (New) A semiconductor device according to claim 1, wherein said semiconductor device comprises a pixel electrode electrically connected to said thin film transistor.

34. (New) A semiconductor device according to claim 2, wherein said semiconductor device comprises a pixel electrode electrically connected to said thin film transistor.

35. (New) A semiconductor device according to claim 3, wherein said semiconductor device comprises a pixel electrode electrically connected to said thin film transistor.

36. (New) A semiconductor device according to claim 4, wherein said semiconductor device comprises a pixel electrode electrically connected to said thin film transistor.

37. (New) A semiconductor device according to claim 21, wherein said semiconductor device comprises a pixel electrode electrically connected to said semiconductor film.

38. (New) A semiconductor device according to claim 22, wherein said semiconductor device comprises a pixel electrode electrically connected to said semiconductor film.